

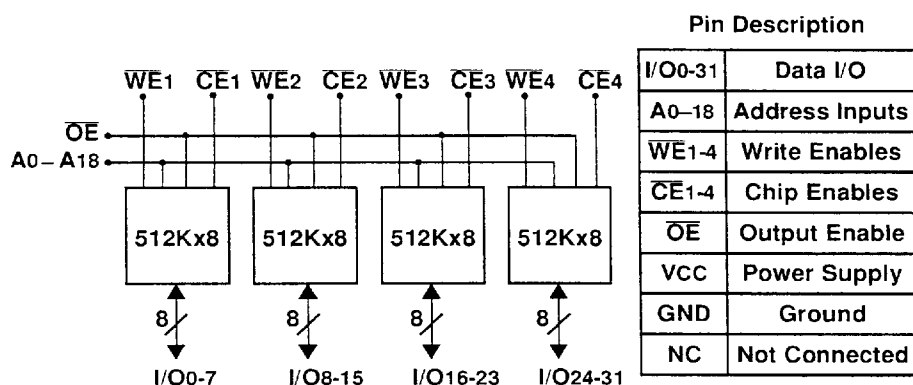
ACT-F512K32 High Speed 16 Megabit FLASH Multichip Module



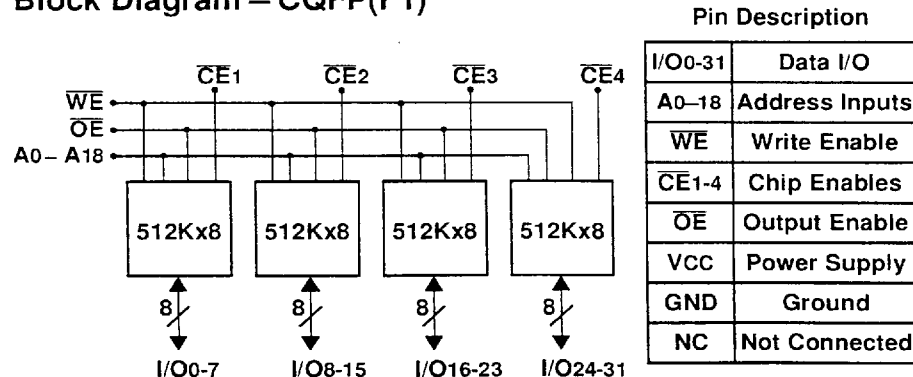
Features

- 4 Low Power 512K x 8 FLASH Die in One MCM Package
- TTL Compatible Inputs and CMOS Outputs
- Access Times of 70, 90, 120 and 150nS
- +5V Programming, 5V \pm 10% Supply
- 100,000 Erase/Program Cycles
- Low Power CMOS, Standby Current 1 mA
- Page Program Operation and Internal Program Control Time
- Sector Architecture (Each Die)
 - 8 Equal size sectors of 64K bytes each
 - Any Combination of Sectors can be Concurrently Erased.
 - Supports Full Chip Erase
- Embedded Erase and Program Algorithms
- MIL-PRF-38534 Compliant MCMs Available
- Industry Standard Pinouts
- Packaging – Hermetic Ceramic
 - 68 Lead, .88" x .88" x .160" Single-Cavity Small Outline gull wing, Aeroflex code# "F5" (*Drops into the 68 Lead JEDEC .99"SQ CQFP footprint*)
 - 66 Pin, 1.08" x 1.08" x .160" PGA Type, No Shoulder, Aeroflex code# "P3"
 - 66 Pin, 1.08" x 1.08" x .160" PGA Type, With Shoulder, Aeroflex code# "P7"
 - 68 Lead, 1.56" x 1.56" x .140" Low Profile CQFP, Aeroflex code# "F1"
- Internal Decoupling Capacitors for Low Noise Operation
- Commercial, Industrial and Military Temperature Ranges
- DESC SMD# 5962-94612
- Released (P3,P7,F5), Pending (F1)

Block Diagram – PGA Type Package(P3,P7) & CQFP(F5)



Block Diagram – CQFP(F1)



General Description

The ACT-F512K32 is a high speed, 16 megabit CMOS flash multichip module (MCM) designed for full temperature range military, space, or high reliability applications.

The MCM can be organized as a 512K x 32bits, 1M x 16bits or 2M x 8bits device and is input TTL and output CMOS compatible. The command register is written by bringing WE to a logic low level (V_{IL}), while CE is low and OE is at logic high level (V_{IH}). Reading is accomplished by chip Enable (CE) and Output Enable (OE) being logically active, see Figure 9. Access time grades of 70nS, 90nS, 120nS and 150nS maximum are standard.

The ACT-F512K32 is packaged in a hermetically

Aeroflex Circuit Technology - Advanced Multichip Modules © 1/14/97

0047156 0000512 294

General Description, Cont'd

sealed co-fired ceramic 66 pin, 1.08"SQ PGA, 68 lead, .88"SQ Ceramic Gull Wing CQFP package or a 68 lead, 1.56"SQ flat package for operation over the temperature range of -55°C to +125°C and military environment.

Each flash memory die is organized as 512K bytes of 8 bits and is designed to be programmed in-system with the standard system 5.0V Vcc supply. A 12.0V VPP is not required for write or erase operations. The MCM can also be reprogrammed with standard EPROM programmers (with the proper socket).

The standard ACT-F512K32 offers access times between 70ns and 150ns, allowing operation of high-speed microprocessors without wait states. To eliminate bus contention, the device has separate chip enable (\overline{CE}) and write enable (\overline{WE}). The ACT-F512K32 is command set compatible with JEDEC standard 4 Mbit EEPROMs. Commands are written to the command register using standard microprocessor write timings. Register contents serve as input to an internal state-machine which controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations.

Reading data out of the device is similar to reading from 12.0V Flash or EPROM devices. The ACT-F512K32 is programmed by executing the program command sequence. This will invoke the Embedded Program Algorithm which is an internal algorithm that automatically times the program pulse widths and verifies proper cell margin. Typically, each sector can be programmed and verified in less than one

(1) second. Erase is accomplished by executing the erase command sequence. This will invoke the Embedded Erase Algorithm which is an internal algorithm that automatically preprograms the array, (if it is not already programmed before) executing the erase operation. During erase, the device automatically times the erase pulse widths and verifies proper cell margin.

Each die in the module or any individual sector of the die is typically erased and verified in 1.5 seconds (if already completely preprogrammed).

Each die also features a sector erase architecture. The sector mode allows for 64K byte blocks of memory to be erased and reprogrammed without affecting other blocks. The ACT-F512K32 is erased when shipped from the factory.

The device features single 5.0V power supply operation for both read and write functions. Internally generated and regulated voltages are provided for the program and erase operations. A low Vcc detector automatically inhibits write operations on the loss of power. The end of program or erase is detected by Data Polling of D7 or by the Toggle Bit feature on D6. Once the end of a program or erase cycle has been completed, the device internally resets to the read mode.

All bits of each die in the ACT-F512K32 can be electrically erased, or all bits within a sector of the die, via Fowler-Nordheim tunneling. Bytes are programmed one byte at a time by hot electron injection.

DESC Standard Military Drawing (SMD) numbers are released.

Absolute Maximum Ratings

Parameter	Range	Units
Case Operating Temperature	-55 to +125	°C
Storage Temperature Range	-65 to +150	°C
Supply Voltage Range (VCC)	-2.0 to +7.0	V
Signal Voltage Range (Any Pin Except A9) Note 1	-2.0 to +7.0	V
Maximum Lead Temperature (10 seconds)	300	°C
Data Retention	10	Years
Endurance (Write/Erase cycles)	100,000 Minimum	
A9 Voltage for sector protect (VID) Note 2	-2.0 to +14.0	V

Note 1. Minimum DC voltage on input or I/O pins is -0.5V. During voltage transitions, inputs may over shoot to -2.0V for periods of up to 20nS. Maximum DC voltage on output and I/O pins is VCC + 0.5V. During voltage transitions, outputs may overshoot to VCC + 2.0V for periods up to 20 nS.

Note 2. Minimum DC input voltage on A9 is -0.5V. During voltage transitions, A9 may overshoot Vss to -2.0V for periods of up to 20 nS. Maximum DC input voltage on A9 is +13.5V which may overshoot to 14.0V for periods up to 20 nS.

Normal Operating Conditions

Symbol	Parameter	Minimum	Maximum	Units
VCC	Power Supply Voltage	+4.5	+5.5	V
VIH	Input High Voltage	+2.0	VCC + 0.5	V
VIL	Input Low Voltage	-0.5	+0.8	V
TA	Operating Temperature (Military)	-55	+125	°C
VID	A9 Voltage for sector protect	11.5	12.5	V

Capacitance

(VIN = 0V, f = 1MHz, TA = 25°C)

Symbol	Parameter	Maximum	Units
CAD	A0 – A16 Capacitance	50	pF
COE	OE Capacitance	50	pF
CWE	Write Enable Capacitance		
	CQFP(F5) Package	20	pF
	CQFP(F1) Package	50	pF
	PGA(P3,P7) Package	20	pF
CCE	Chip Enable Capacitance	20	pF
CI/O	I/O0 – I/O31 Capacitance	20	pF

Parameters Guaranteed but not tested

DC Characteristics – CMOS Compatible

(VCC = 5.0V, Vss = 0V, TA = -55°C to +125°C)

Parameter	Sym	Conditions	Speeds 70, 90, 120 & 150nS		
			Minimum	Maximum	Units
Input Leakage Current	ILI	VCC = 5.5V, VIN = GND to VCC		10	µA
Output Leakage Current	ILOx32	VCC = 5.5V, VIN = GND to VCC		10	µA
Active Operating Supply Current for Read (1)	Icc1	CE = VIL, OE = VIH, f = 5MHz		190	mA
Active Operating Supply Current for Program or Erase(2)	Icc2	CE = VIL, OE = VIH		240	mA
Standby Supply Current	Icc4	VCC = 5.5V, CE = VIH, f = 5MHz		6.5	mA
Static Supply Current	Icc3	VCC = 5.5V, CE = VIH		0.6	mA
Output Low Voltage	VOL	IOL = +12.0 mA, VCC = 4.5V		0.45	V
Output High Voltage	VOH1	IOH = -2.5 mA, VCC = 4.5V	0.85 x VCC		V
Low Power Supply Lock-Out Voltage	VLKO		3.2	4.2	V

Note 1. The Icc current listed includes both the DC operating current and the frequency dependent component (At 5 MHz). The frequency component typically is less than 2 mA/MHz, with OE at VIN.

Note 2. Icc active while Embedded Algorithm (Program or Erase) is in progress.

Note 3. DC Test conditions: VIL = 0.3V, VIN = VCC - 0.3V

AC Characteristics – Read Only Operations

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol		-70		-90		-120		-150		Units
	JEDEC	Stand'd	Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{AVAV}	t _{RC}	70		90		120		150		nS
Address Access Time	t _{AVQV}	t _{ACC}		70		90		120		150	nS
Chip Enable Access Time	t _{ELQV}	t _{CE}		70		90		120		150	nS
Output Enable to Output Valid	t _{GLQV}	t _{OE}		35		35		50		55	nS
Chip Enable to Output High Z (1)	t _{EHQZ}	t _{DF}		20		20		30		35	nS
Output Enable High to Output High Z(1)	t _{GHQZ}	t _{DF}		20		20		30		35	nS
Output Hold from Address, \overline{CE} or \overline{OE} Change, Whichever is First	t _{AXQX}	t _{OH}	0		0		0		0		nS

Note 1. Guaranteed by design, but not tested.

AC Characteristics – Write/Erase/Program Operations, \overline{WE} Controlled

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol		-70		-90		-120		-150		Units
	JEDEC	Stand'd	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{AVAC}	t _{WC}	70		90		120		150		nS
Chip Enable Setup Time	t _{ELWL}	t _{CE}	0		0		0		0		nS
Write Enable Pulse Width	t _{WLWH}	t _{WP}	45		45		50		50		nS
Address Setup Time	t _{AVWL}	t _{AS}	0		0		0		0		nS
Data Setup Time	t _{DVWH}	t _{DS}	45		45		50		50		nS
Data Hold Time	t _{WHDX}	t _{DH}	0		0		0		0		nS
Address Hold Time	t _{WLAX}	t _{AH}	45		45		50		50		nS
Write Enable Pulse Width High	t _{WHWL}	t _{WPH}	20		20		20		20		nS
Duration of Byte Programming Operation Typ = 16 μ S	t _{WHWH1}		16		16		16		16		μ S
Chip Erase Time	t _{WHWH2}		14	120	14	120	14	120	14	120	Sec
Sector Erase Time			1.5	30	1.5	30	1.5	30	1.5	30	Sec
Read Recovery Time before Write	t _{GHWL}		0		0		0		0		μ S
V _{CC} Setup Time (2)		t _{VCE}	50		50		50		50		μ S
Chip Programming Time				50		50		50		50	Sec
Output Enable Setup Time		t _{OES}	0		0		0		0		nS
Output Enable Hold Time (1) (2)		t _{OEH}	10		10		10		10		nS

Notes: 1. For Toggle and Data Polling. 2. Guaranteed by design, but not tested.

AC Characteristics – Write/Erase/Program Operations, \overline{CE} Controlled

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol		-70		-90		-120		-150		Units
	JEDEC	Stand'd	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{AVAC}	t _{WC}	70		90		120		150		nS
Write Enable Setup Time	t _{WLLEL}	t _{WS}	0		0		0		0		nS
Chip Enable Pulse Width	t _{LEH}	t _{CP}	45		45		50		55		nS
Address Setup Time	t _{AVEL}	t _{AS}	0		0		0		0		nS
Data Setup Time	t _{DVEH}	t _{DS}	45		45		50		55		nS
Data Hold Time	t _{EHDX}	t _{DH}	0		0		0		0		nS
Address Hold Time	t _{ELAX}	t _{AH}	45		45		50		55		nS
Chip Enable Pulse Width High	t _{HEH}	t _{CPH}	20		20		20		20		nS
Duration of Byte Programming	t _{WHWH1}		16		16		16		16		μ S
Chip Erase Time	t _{WHWH2}		14	120	14	120	14	120	14	120	Sec
Sector Erase Time			1.5	30	1.5	30	1.5	30	1.5	30	Sec
Read Recovery Time Before Write	t _{GHLEL}		0		0		0		0		μ S
Chip Programming Time				50		50		50		50	Sec

Device Operation

The ACT-F512K32 MCM is composed of four (4), four (4) megabit Flash chips. The following description is for the individual flash device, is applicable to each of the four memory chips inside the MCM. Chip 1 is distinguished by \overline{CE}_1 and I/O₁₋₇, Chip 2 by \overline{CE}_2 and I/O₈₋₁₅, Chip 3 by \overline{CE}_3 and I/O₁₆₋₂₃, and Chip 4 by \overline{CE}_4 and I/O₂₄₋₃₁.

Programming of the ACT-F512K32 is accomplished by executing the program command sequence. The program algorithm, which is an internal algorithm, automatically times the program pulse widths and verifies proper cell status. Sectors can be programmed and verified in less than one (1) second. Erase is accomplished by executing the erase command sequence. The erase algorithm, which is internal, automatically preprograms the array if it is not already programmed before executing the erase operation. During erase, the device automatically times the erase pulse widths and verifies proper cell status. The entire memory is typically erased and verified in 1.5 seconds (if pre-programmed). The sector mode allows for 64K byte blocks of memory to be erased and reprogrammed without affecting other blocks.

Bus Operation

READ

The ACT-F512K32 has two control functions, both of which must be logically active, to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Output-Enable (\overline{OE}) is the output control and should be used to gate data to the output pins of the chip selected. Figure 7 illustrates AC read timing waveforms.

OUTPUT DISABLE

With Output-Enable at a logic high level (V_{IH}), output from the device is disabled. Output pins are placed in a high impedance state.

STANDBY MODE

The ACT-F512K32 standby mode consumes less than 6.5 mA. In the standby mode the outputs are in a high impedance state, independent of the \overline{OE} input. If the device is deselected during erasure or programming, the device will draw active current until the operation is completed.

WRITE

Device erasure and programming are accomplished via the command register. The contents of the register serve as input to the internal state machine. The state machine outputs dictate the function of the device.

The command register itself does not occupy an addressable memory location. The register is a latch used to store the command, along with address and data information needed to execute the command. The command register is written by bringing \overline{WE} to a logic low level (V_{IL}), while \overline{CE} is low and \overline{OE} is at V_{IH} . Addresses are latched on the falling edge of \overline{WE} or \overline{CE} , whichever happens later. Data is latched on the rising edge of the \overline{WE} or \overline{CE} whichever occurs first. Standard microprocessor write timings are used. Refer to AC Program Characteristics and Waveforms, Figures 3, 8 and 13.

Command Definitions

Device operations are selected by writing specific address and data sequences into the command register. Table 3 defines these register command sequences.

READ/RESET COMMAND

The read or reset operation is initiated by writing the read/reset command sequence into the command register. Microprocessor read cycles retrieve array data from the memory. The device remains enabled for reads until the command register contents are altered.

The device will automatically power-up in the read/reset state. In this case, a command sequence

Table 1 – Bus Operations

Operation	\overline{CE}	\overline{OE}	\overline{WE}	A0	A1	A6	A9	I/O
READ	L	L	H	A0	A1	A6	A9	DOUT
STANDBY	H	X	X	X	X	X	X	HIGH Z
OUTPUT DISABLE	L	H	H	X	X	X	X	HIGH Z
WRITE	L	H	L	A0	A1	A6	A9	DIN
ENABLE SECTOR PROTECT	L	V_{ID}	L	X	X	X	V_{ID}	X
VERIFY SECTOR PROTECT	L	L	H	L	H	L	V_{ID}	Code

Table 2 – Sector Addresses Table

	A18	A17	A16	Address Range
SA0	0	0	0	00000h – 0FFFFh
SA1	0	0	1	10000h – 1FFFFh
SA2	0	1	0	20000h – 2FFFFh
SA3	0	1	1	30000h – 3FFFFh
SA4	1	0	0	40000h – 4FFFFh
SA5	1	0	1	50000h – 5FFFFh
SA6	1	1	0	60000h – 6FFFFh
SA7	1	1	1	70000h – 7FFFFh

Table 3 — Commands Definitions

Command Sequence	Bus Write Cycles	First Bus Write Cycle		Second Bus Write Cycle		Third Bus Write Cycle		Fourth Bus Read/Write Cycle		Fifth Bus Write Cycle		Sixth Bus Write Cycle	
Required		Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
Read/Reset	1	XXXH	F0H										
Read/Reset	4	5555H	AAH	2AAAH	55H	5555H	F0H	RA	RD				
Autoselect	4	5555H	AAH	2AAAH	55H	5555H	90H						
Byte Program	6	5555H	AAH	2AAAH	55H	5555H	A0H	PA	PD				
Chip Erase	6	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	5555H	10H
Sector Erase	6	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	SA	30H
Sector Erase Suspend	Erase can be suspended during sector erase with Address (Don't care), Data (B0H)												
Sector Erase Resume	Erase can be resumed after suspend with Address (Don't care), Data (30H)												

NOTES:

1. Address bit A15, A16, A17 and A18 = X = Don't Care. Write Sequences may be initiated with A15 in either state.
2. Address bit A15, A16, A17 and A18 = X = Don't Care for all address commands except for Program Address (PA) and Sector Address (SA).
3. RA = Address of the memory location to be read
PA = Address of the memory location to be programmed. Addresses are latched on the falling edge of the WE pulse.
SA = Address of the sector to be erased. The combination of A18, A17, A16 will uniquely select any sector.
4. RD = Data read from location RA during read Operation.
PD = Data to be programmed at location PA. Data is latched on the rising edge of WE.

is not required to read data. Standard microprocessor read cycles will retrieve array data. The device will automatically power-up in the read/reset state. In this case, a command sequence is not required to read data. Standard Microprocessor read cycles will retrieve array data. This default value ensures that no spurious alteration of the memory content occurs during the power transition. Refer to the AC Read Characteristics and Figure 7 for the specific timing parameters.

BYTE PROGRAMING

The device is programmed on a byte-by-byte basis. Programming is a four bus cycle operation. There are two "unlock" write cycles. These are followed by the program set-up command and data write cycles. Addresses are latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs later, while the data is latched on the rising edge of \overline{CE} or \overline{WE} whichever occurs first. The rising edge of \overline{CE} or \overline{WE} (whichever occurs first) begins programming. Upon executing the Embedded Program Algorithm command sequence the system is *not* required to provide further controls or timings. The device will automatically provide adequate internally generated program pulses and verify the programmed cell margin. The automatic programming operation is completed when the data on D7 is equivalent to data written to this bit at which time the device returns to the read mode and addresses are no longer latched. Therefore, the device requires that a valid address to the device be supplied by the System at this time. Data Polling must be performed at the memory location which is being programmed.

Programming is allowed in any sequence and across sector boundaries. Beware that a data "0" cannot be programmed back to a "1". Attempting to do so may cause the device to exceed programming time limits (D5 = 1) or result in an apparent success, according to the data polling algorithm, but a read from reset/read mode will show that the data is still "0".

Only erase operations can convert "0"s to "1"s.

Figure 3, 8 and 13 illustrates the programming algorithm using typical command strings and bus operations.

CHIP ERASE

Chip erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the chip erase command.

Chip erase does *not require* the user to program the Embedded Erase Algorithm (Figure 4) sequence the device automatically will program and verify the entire memory for an all zero data pattern prior to electrical erase. The chip erase is performed sequentially one sector at a time. *Note: Post Erase data state is all "1"s.* The system is not required to provide any controls or timings during these operations.

The automatic erase begins on the rising edge of the last \overline{WE} pulse in the command sequence and terminates when the data in D7 is "1" (see Write Operation Status section - Table 4) at which time the device returns to read the mode. See Figures 4 and 9.

SECTOR ERASE

Sector erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "setup" command. Two more "unlock" write cycles are then followed by the sector erase command. The sector address (any address location within the desired sector) is latched on the falling edge of \overline{WE} , while the command (data) is latched on the rising edge of \overline{WE} . A time-out of 80 μ s from the rising edge of the last sector erase command will initiate the sector erase command(s). **Please note:** *Do not attempt to write an invalid command*

sequence during the sector erase operation. otherwise, it will terminate the sector erase operation and the device will reset back into the read mode.

Multiple sectors may be erased concurrently by writing the six bus cycle operations as described above. This sequence is followed with writes of the sector erase command (30H) to addresses in other sectors desired to be concurrently erased. The time between writes must be less than 80µs, otherwise that command will not be accepted. A time-out of 80µs from the rising edge of the \overline{WE} pulse for the last sector erase command will initiate the sector erase. If another sector erase command is written within the 80µs time-out window the timer is reset. Any command other than sector erase within the time-out window will reset the device to the read mode, ignoring the previous command string. Loading the sector erase buffer may be done in any sequence and with any number of sectors (1 to 8).

Sector erase does *not* require the user to program the device prior to erase. The device automatically programs all memory locations in the sector(s) to be erased prior to electrical erase. When erasing a sector or sectors the remaining unselected sectors are not affected. The system is *not* required to provide any controls or timings during these operations. Post Erase data state is all "1"s.

The automatic sector erase begins after the 80µs time out from the rising edge of the \overline{WE} pulse for the last sector erase command pulse and terminates when the data on D7 is "1" at which time the device returns to read mode. *During the execution of the Sector Erase command, only the Erase Suspend and Erase Resume commands are allowed. All other commands will reset the device to read mode.* Data Polling must be performed at an address within any of the sectors being erased.

Data Protection

The ACT-F512K32 is designed to offer protection against accidental erasure or programming caused by spurious system level singles that may exist during power transitions. During power up the device automatically resets the internal state machine in the read mode. Also, with its control register architecture, alteration of the memory content only occurs after successful completion of specific multi-bus cycle command sequences.

The device also incorporates several features to prevent inadvertent write cycles resulting from Vcc power-up and power-down transitions or system noise.

LOW Vcc WRITE INHIBIT

To avoid initiation of a write cycle during Vcc power-up and power-down, a write cycle is locked out for Vcc less than 3.2V (typically 3.7V). If $V_{cc} < V_{LKO}$, the command register is disabled and all internal program/erase circuits are disabled. Under this condition the device will reset to read mode. Subsequent writes will be ignored until the Vcc level

is greater than V_{LKO} . It is the users responsibility to ensure that the control pins are logically correct to prevent unintentional writes when Vcc is above 3.2V.

WRITE PULSE GLITCH PROTECTION

Noise pulses of less than 5nS (typical) on \overline{OE} , \overline{CE} or \overline{WE} will not initiate a write cycle.

LOGICAL INHIBIT

Writing is inhibited by holding anyone of $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IH}$. To initiate a write cycle \overline{CE} and \overline{WE} must be logical zero while \overline{OE} is a logical one.

POWER-UP WRITE INHIBIT

Power-up of the device with $\overline{WE} = \overline{CE} = V_{IL}$ and $\overline{OE} = V_{IH}$ will not accept commands on the rising edge of \overline{WE} . The internal state machine is automatically reset to the read mode on power-up.

Write Operation Status

D7

DATA POLLING

The ACT-F512K32 features Data Polling as a method to indicate to the host that the internal algorithms are in progress or completed. During the program algorithm, an attempt to read the device will produce compliment data of the data last written to D7. During the erase algorithm, an attempt to read the device will produce a "0" at the D7 Output. Upon completion of the erase algorithm an attempt to read the device will produce a "1" at the D7 Output.

For chip Erase, the Data Polling is valid after the rising edge of the sixth \overline{WE} pulse in the six write pulse sequence. For sector erase, the Data Polling is valid after the last rising edge of the sector erase \overline{WE} pulse. Data polling must be performed at a sector address within any of the sectors being erased and not a protected sector. Otherwise, the status may not be valid. Once the algorithm operation is close to being completed, data pins (D7) change asynchronously while the output enable (\overline{OE}) is asserted low. This means that the device is driving status information on D7 at one instance of time and then that byte's valid data at the next instant of time. Depending on when the system samples the D7 Output, it may read the status or valid data. Even if the device has completed internal algorithm operation and D7 has a valid data, the data outputs on D0 - D6 may be still invalid. The valid data on D0 - D7 will be read on the successive read attempts. The Data Polling feature is only active during the programming algorithm, erase algorithm, or sector erase time-out.

See Figures 6 and 10

D6

TOGGLE BIT

The ACT-F512K32 also features the "Toggle Bit" as a method to indicate to the host system that algorithms are in progress or completed.

During a program or erase algorithm cycle, successive attempts to read data from the device will result in D6 toggling between one and zero. Once the program or erase algorithm cycle is completed, D6 will stop toggling and valid data will be read on successive attempts. During programming the Toggle Bit is valid after the rising edge of the fourth WE pulse in the four write pulse sequence. For chip erase the Toggle Bit is valid after the rising edge of the sixth WE pulse in the six write pulse sequence. For Sector erase, the Toggle Bit is valid after the last rising edge of the sector erase WE pulse. The Toggle Bit is active during the sector time out. See Figure 1 and 5.

D5

EXCEEDED TIMING LIMITS

D5 will indicate if the program or erase time has exceeded the specified limits. Under these conditions D5 will produce a "1". The Program or erase cycle was not successfully completed. Data Polling is the only operation function of the device under this condition. The CE circuit will partially power down the device under these conditions by approximately 8 mA per chip. The OE and WE pins will control the output disable functions as shown in Table 1. To reset the device, write the reset command sequence to the device. This allows the system to continue to use the other active sectors in the device.

D3

SECTOR ERASE TIMER

After the completion of the initial sector erase command sequence the sector erase time-out will begin. D3 will remain low until the time-out is complete. Data Polling and Toggle Bit are valid after the initial sector erase command sequence.

If Data Polling or the Toggle Bit indicates the device has been written with a valid erase command, D3 may be used to determine if the sector erase timer window is still open. If D3 is high ("1") the internally controlled erase cycle has begun; attempts to write subsequent commands to the device will be ignored until the erase operation is completed as indicated by Data Polling or Toggle Bit. If D3 is low ("0"), the device will accept additional sector erase commands. To ensure the command has been accepted, the software should check the status of D3 prior to and

following each subsequent sector erase command. If D3 were high on the second status check, the command may not have been accepted. See Table 4

Sector Protection Algorithms

SECTOR PROTECTION

The ACT-F512K32 features hardware sector protection which will disable both program and erase operations to an individual sector or any group of sectors. To activate this mode, the programming equipment must force Vid on control pin OE and address pin A9. The sector addresses should be set using higher address lines A18, A17, and A16. The protection mechanism begins on the falling edge of the WE pulse and is terminated with the rising edge of the same.

To verify programming of the protection circuitry, the programming equipment must force Vid on address pin A9 with CE and OE at VIL and WE at VIH. Scanning the sector addresses (A16, A17, and A18) while (A6, A1, A0) = (0, 1, 0,) will produce a logical "1" code at device output D0 for a protected sector. Otherwise the device will read 00H for unprotected sector. In this mode, the lower order addresses, except for 0, A1, and A6 are don't care.

It is also possible to verify if a sector is protected during the sector protection operation. This is done by setting A6 = CE = OE = VIL and WE = VIH (A9 remains high at Vid). Reading the device at address location XXX2H, where the higher order addresses (A18, A17, and A16) define a particular sector, will produce 01H at data outputs (D0 - D7) for a protected sector.

SECTOR UNPROTECT

The ACT-F512K32 also features a sector unprotect mode, so that a protected sector may be unprotected to incorporate any changes in the code. All sectors should be protected prior to unprotecting any sector.

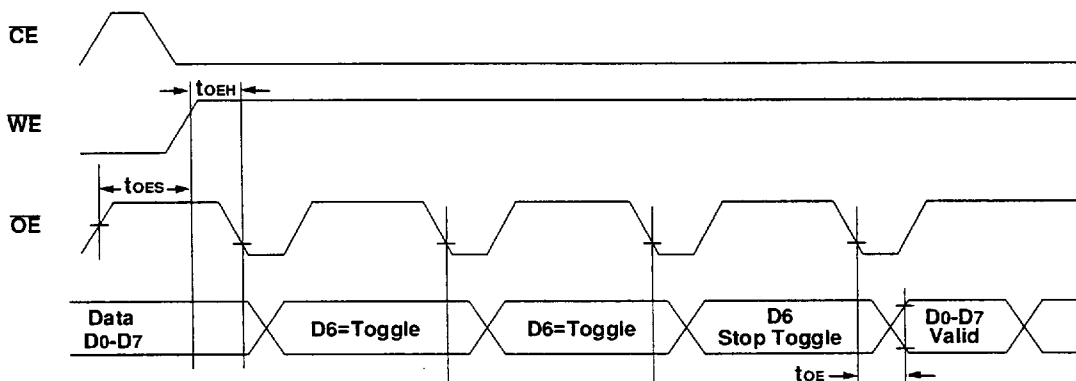
To activate this mode, the programming equipment must force Vid on control pins OE, CE, and address pin A9. The address pins A6, A16, and A12 should be set to VIH. The unprotection mechanism begins on the falling edge of the WE pulse and is terminated with the rising edge of the same.

It is also possible to determine if a sector is unprotected in the system by writing the autoselect command and A6 is set at VIH. Performing a read operation at address location XXX2H, where the higher order addresses (A18, A17, and A16) define a particular sector address, will produce 00H at data outputs (D0-D7) for an unprotected sector.

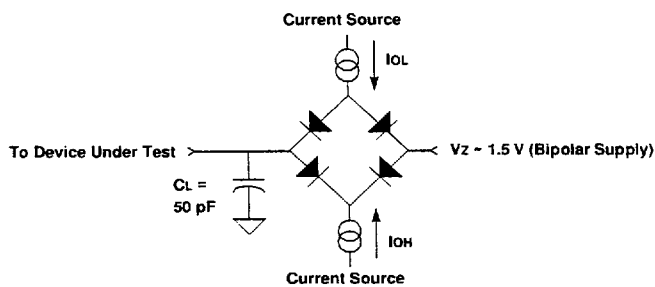
Table 4 — Hardware Sequence Flags

In Progress	Status	D7	D6	D5	D3	D2 – D0
	Auto-Programming	D7	Toggle	0	0	D
	Programming in Auto Erase	0	Toggle	0	1	
Exceeding Time Limits	Auto-Programming	D7	Toggle	1	1	D
	Programming in Auto Erase	0	Toggle	1	1	

**Figure 1
AC Waveforms for Toggle Bit During Embedded Algorithm Operations**



**Figure 2
AC Test Circuit**



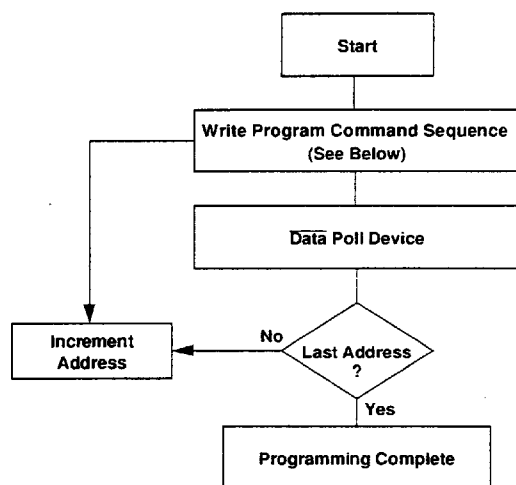
Parameter	Typical	Units
Input Pulse Level	0 – 3.0	V
Input Rise and Fall	5	nS
Input and Output Timing Reference	1.5	V
Output Lead Capacitance	50	pF

Notes:

- 1) VZ is programmable from -2V to +7V.
- 2) IOL and IOH programmable from 0 to 16 mA.
- 3) Tester Impedance Zo = 75Ω.
- 4) VZ is typically the midpoint of VOH and VOL.
- 5) IOL and IOH are adjusted to simulate a typical resistance load circuit.
- 6) ATE Tester includes jig capacitance.

Figure 3
Programming Algorithm

Bus Operations	Command Sequence	Comments
Standby		
Write	Program	Valid Address/Data Sequence
Read		Data Polling to Verify Programming
Standby		Compare Data Output to Data Expected



Program Command Sequence (Address/Command):

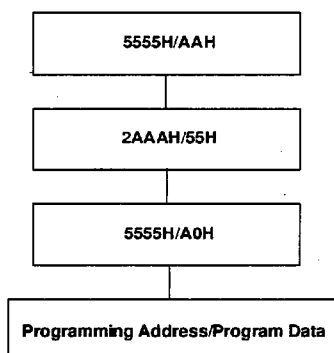
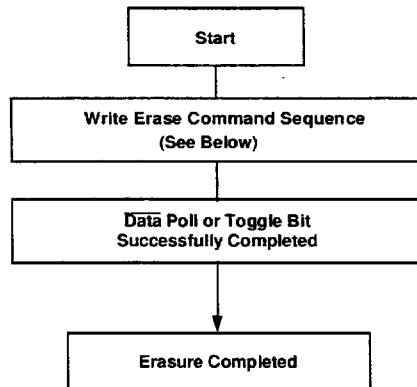
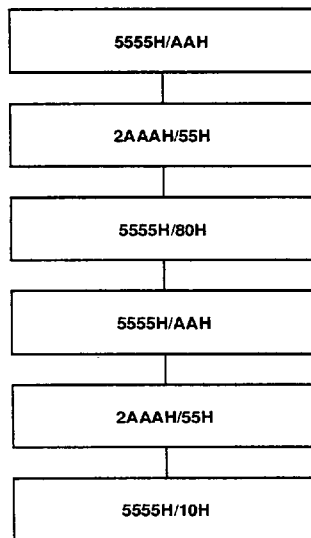


Figure 4
Erase Algorithm

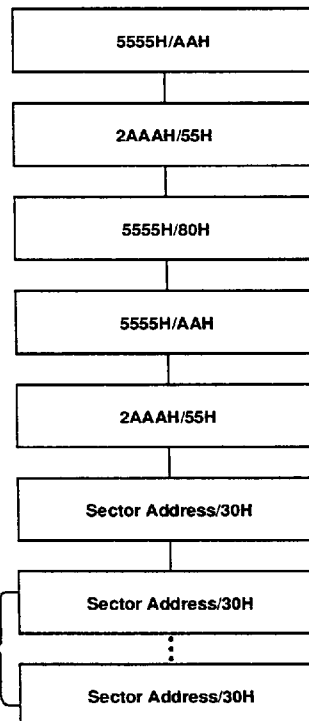
Bus Operations	Command Sequence	Comments
Standby		
Write	Erase	
Read		Data Polling to Verify Erasure
Standby		Compare Output to FFH



**Chip Erase Command Sequence
(Address/Command)**

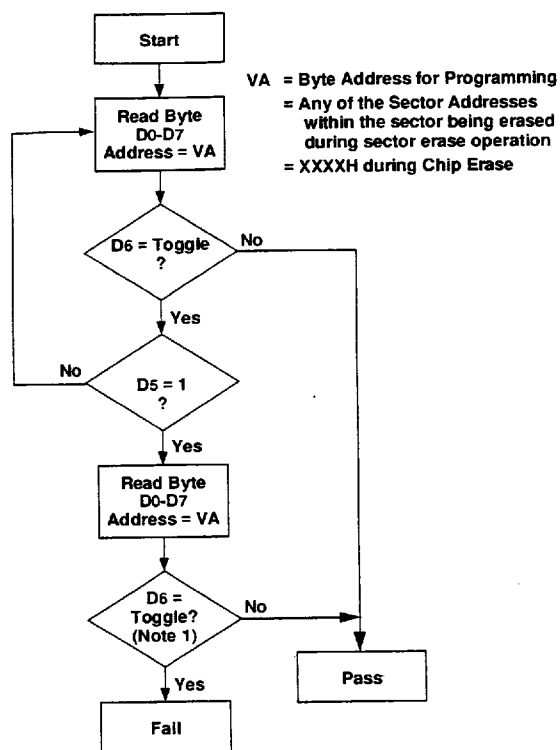


**Individual Sector/Multiple Sector
Erase Command Sequence
(Address/Command)**



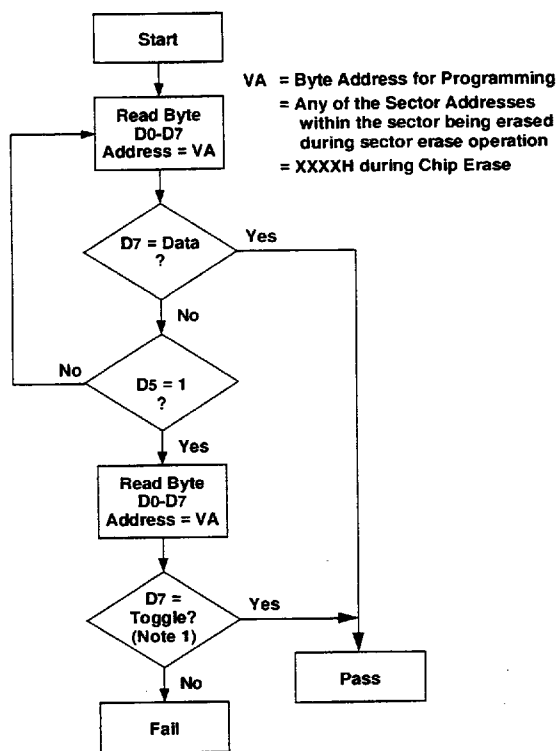
Additional Sector
Erase Commands
are Optional

Figure 5 Toggle Bit Algorithm



Note 1. D6 is rechecked even if D5 = "1" because D6 may stop toggling at the same time as D5 changes to "1".

Figure 6 Data Polling Algorithm



Note 1. D7 is rechecked even if D5 = "1" because D7 may change simultaneously with D5.

AC Waveforms for Read Operations

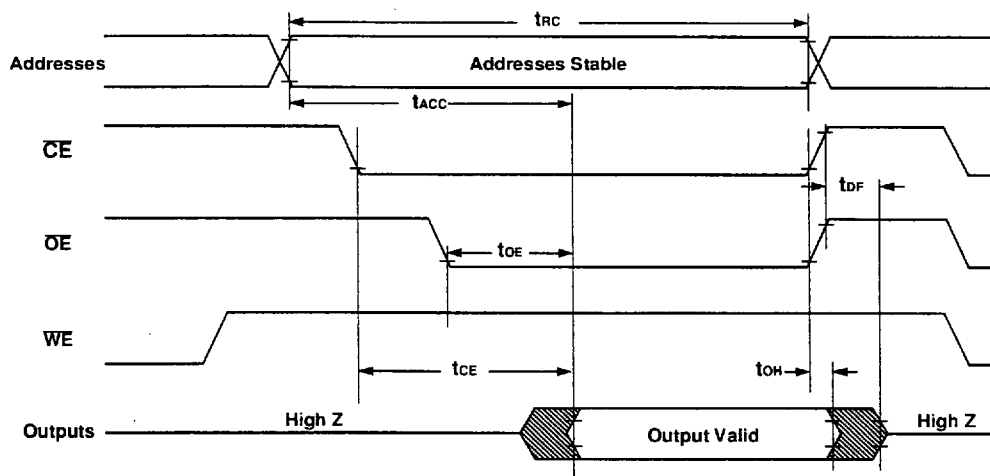
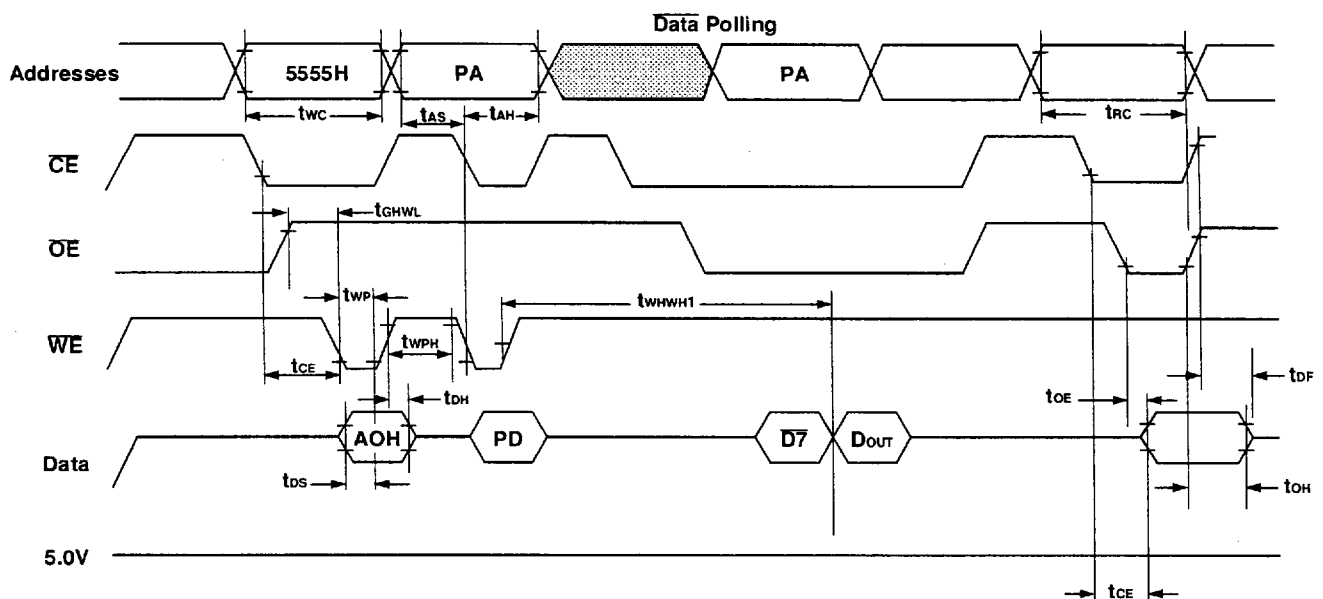


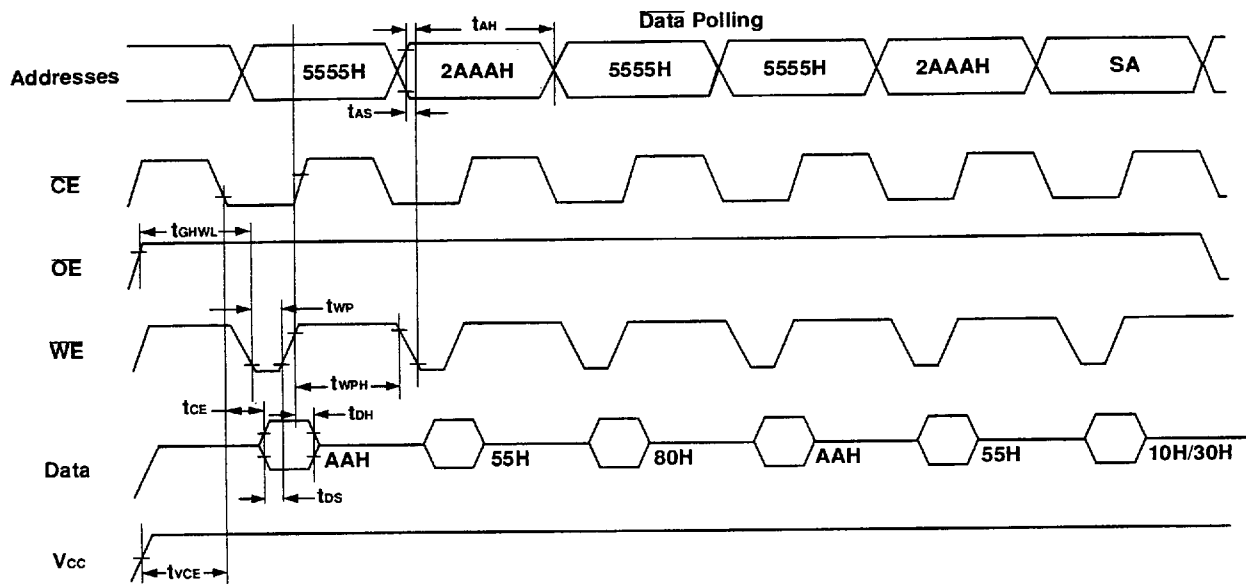
Figure 8
Write/Erase/Program
Operation, WE Controlled



Notes:

1. PA is the address of the memory location to be programmed.
2. PD is the data to be programmed at byte address.
3. D7 is the Output of the complement of the data written to the device.
4. Dout is the output of the data written to the device.
5. Figure indicates last two bus cycles of four bus cycle sequence.

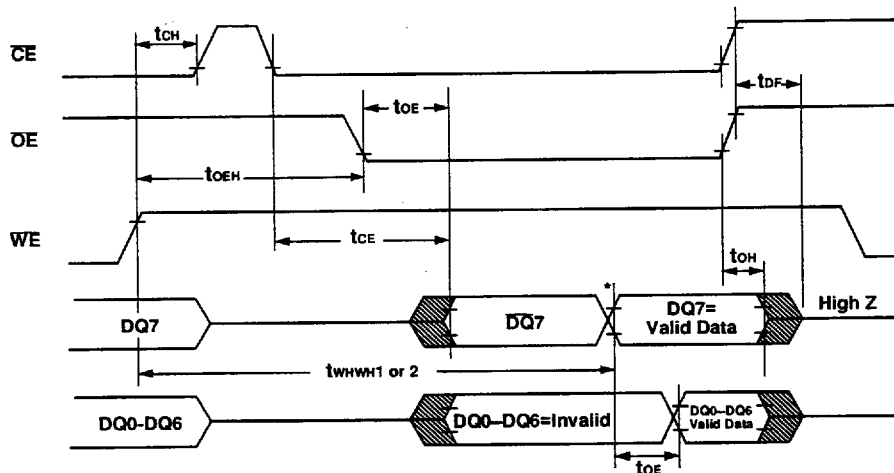
Figure 9 AC Waveforms Chip/Sector Erase Operations



Notes:

1. SA is the sector address for sector erase.

Figure 10
AC Waveforms for Data Polling
During Embedded Algorithm Operations



* DQ7=Valid Data (The device has completed the Embedded operation).

Figure 11
Sector Protection Algorithm

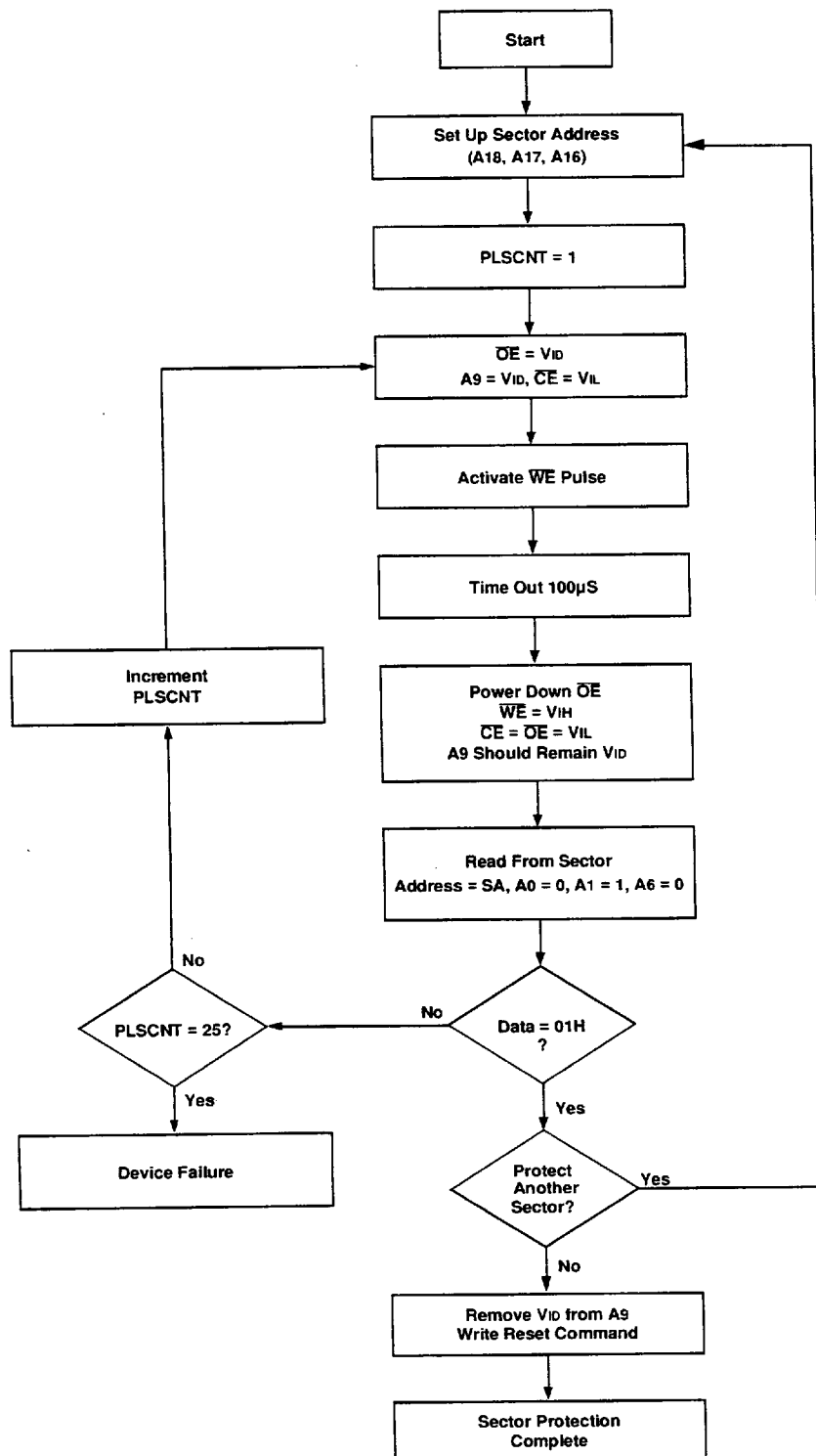
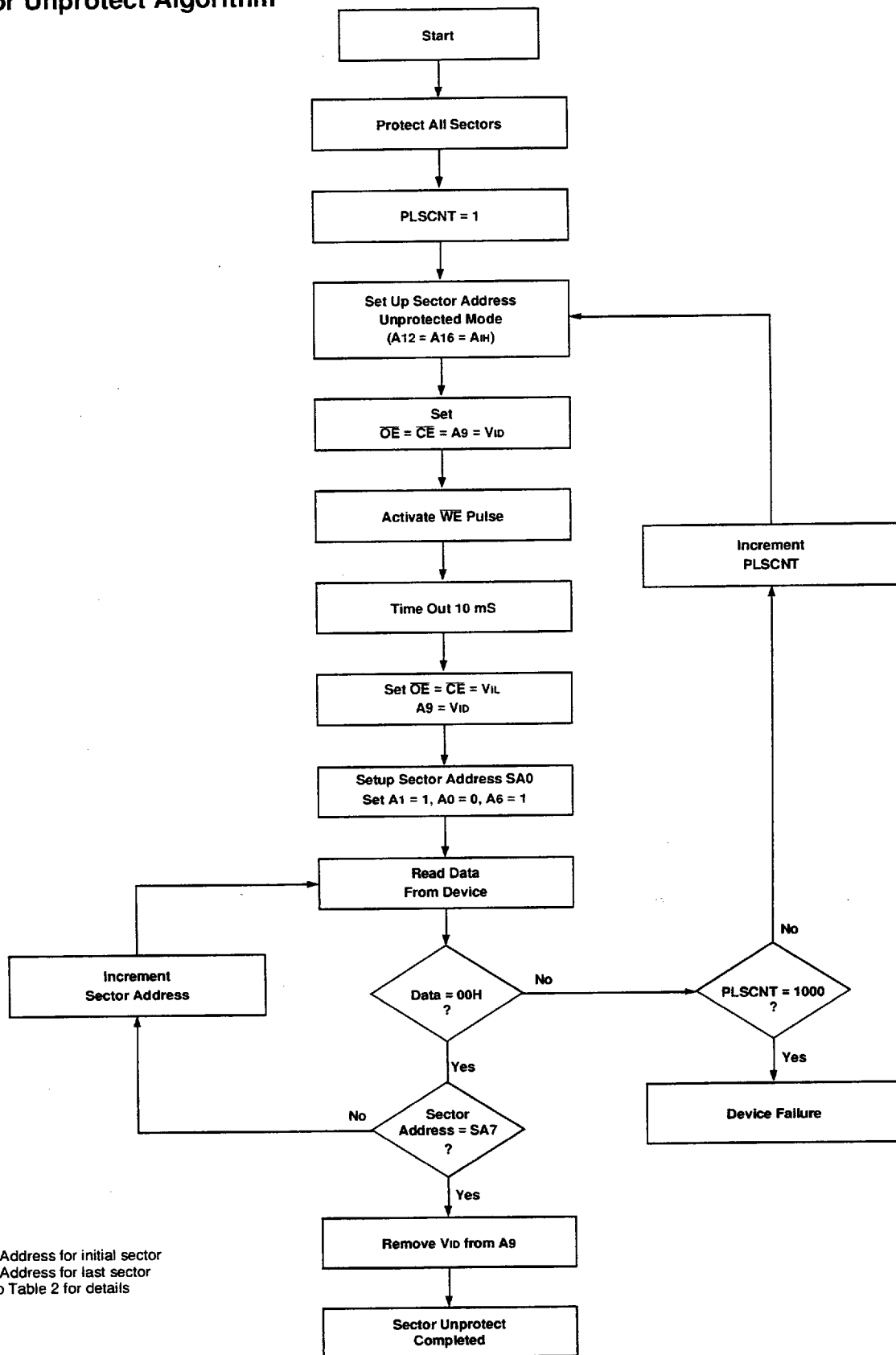
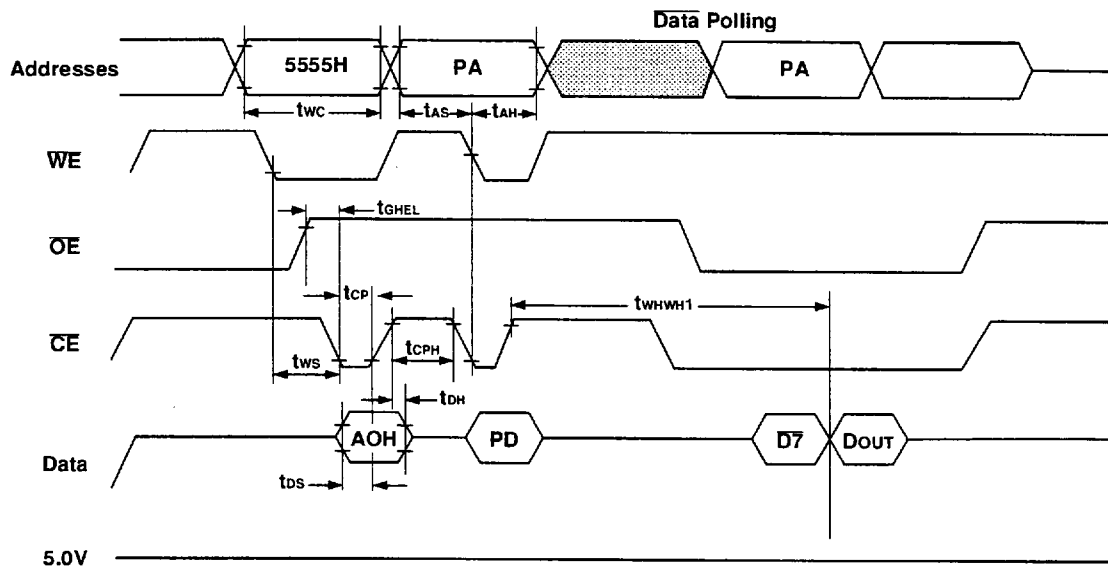


Figure 12
Sector Unprotect Algorithm



Notes:
SA0 = Sector Address for initial sector
SA7 = Sector Address for last sector
Please refer to Table 2 for details

Figure 13
Alternate \overline{CE} Controlled Programming Operation Timings



Notes:

1. PA is the address of the memory location to be programmed.
2. PD is the data to be programmed at byte address.
3. $\overline{D7}$ is the Output of the complement of the data written to the device.
4. DOUT is the output of the data written to the device.
5. Figure indicates last two bus cycles of four bus cycle sequence.

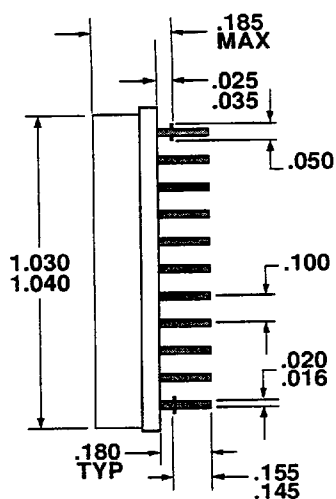
Pin Numbers & Functions

66 Pins — PGA							
Pin#	Function	Pin#	Function	Pin#	Function	Pin#	Function
1	I/O8	18	A15	35	I/O25	52	WE3
2	I/O9	19	Vcc	36	I/O26	53	CE3
3	I/O10	20	CE1	37	A7	54	GND
4	A14	21	NC	38	A12	55	I/O19
5	A16	22	I/O3	39	NC	56	I/O31
6	A11	23	I/O15	40	A13	57	I/O30
7	A0	24	I/O14	41	A8	58	I/O29
8	A18	25	I/O13	42	I/O16	59	I/O28
9	I/O0	26	I/O12	43	I/O17	60	A1
10	I/O1	27	OE	44	I/O18	61	A2
11	I/O2	28	A17	45	Vcc	62	A3
12	WE2	29	WE1	46	CE4	63	I/O23
13	CE2	30	I/O7	47	WE4	64	I/O22
14	GND	31	I/O6	48	I/O27	65	I/O21
15	I/O11	32	I/O5	49	A4	66	I/O20
16	A10	33	I/O4	50	A5		
17	A9	34	I/O24	51	A6		

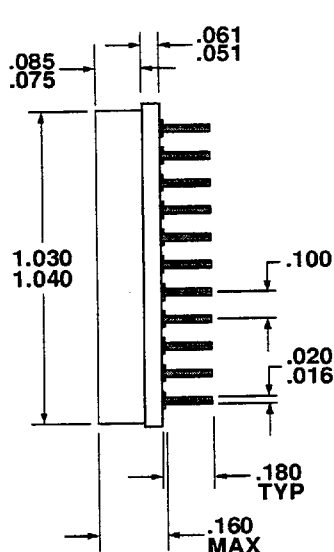
"P3" — 1.08" SQ PGA Type (without shoulder) Package

"P7" — 1.08" SQ PGA Type (with shoulder) Package

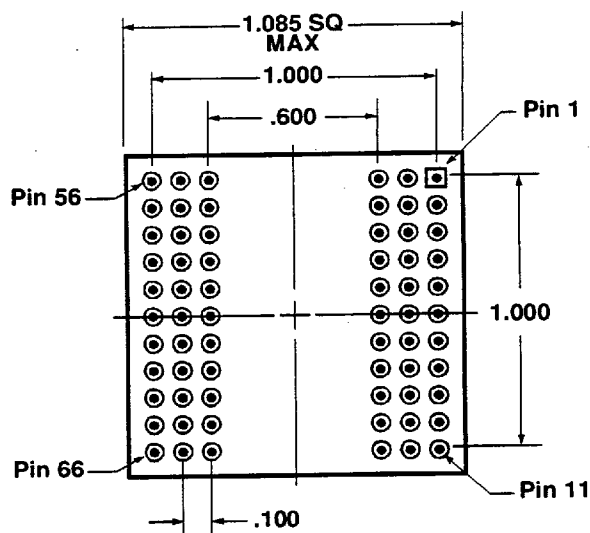
Side View
(P7)



Side View
(P3)



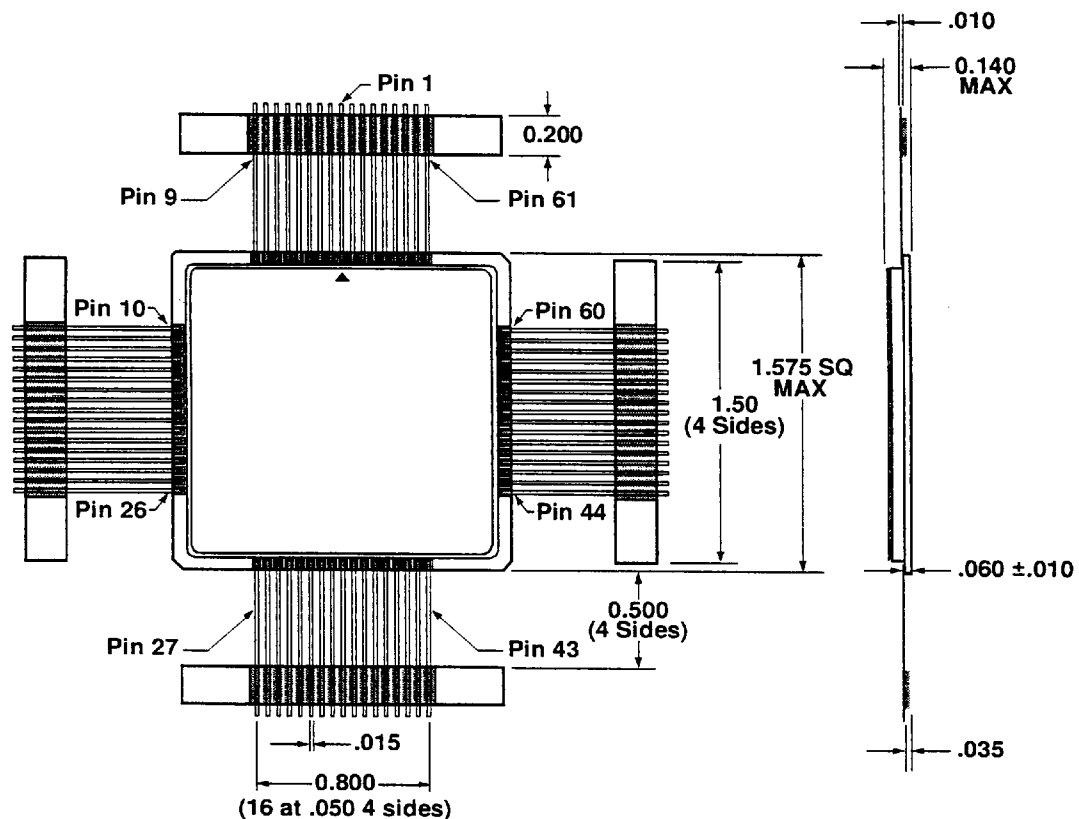
Bottom View (P7 & P3)



Pin Numbers & Functions

68 Pins — CQFP							
Pin #	Function	Pin #	Function	Pin #	Function	Pin #	Function
1	GND	18	GND	35	\overline{OE}	52	GND
2	\overline{CE}_1	19	I/O8	36	\overline{CE}_4	53	I/O23
3	A5	20	I/O9	37	A17	54	I/O22
4	A4	21	I/O10	38	A18	55	I/O21
5	A3	22	I/O11	39	NC	56	I/O20
6	A2	23	I/O12	40	NC	57	I/O19
7	A1	24	I/O13	41	NC	58	I/O18
8	A0	25	I/O14	42	NC	59	I/O17
9	NC	26	I/O15	43	NC	60	I/O16
10	I/O0	27	V _{CC}	44	I/O31	61	V _{CC}
11	I/O1	28	A11	45	I/O30	62	A10
12	I/O2	29	A12	46	I/O29	63	A9
13	I/O3	30	A13	47	I/O28	64	A8
14	I/O4	31	A14	48	I/O27	65	A7
15	I/O5	32	A15	49	I/O26	66	A6
16	I/O6	33	A16	50	I/O25	67	WE
17	I/O7	34	\overline{CE}_2	51	I/O24	68	\overline{CE}_3

"F1"— CQFP Flat Package



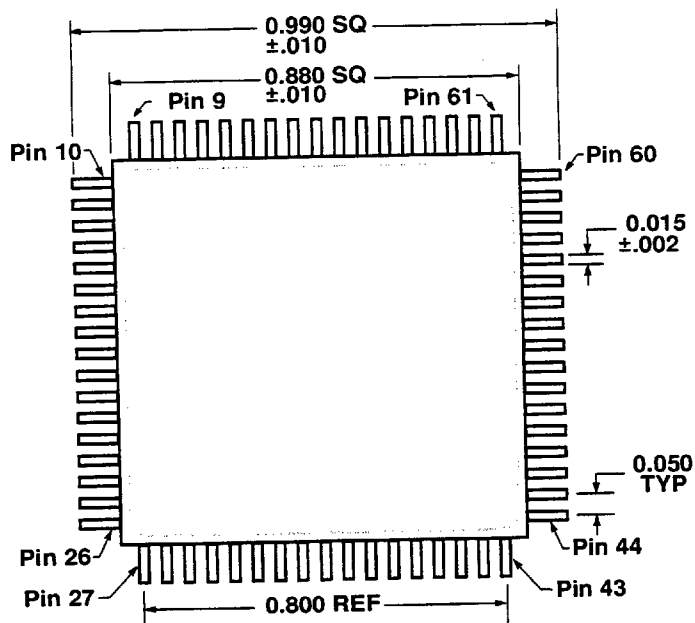
Pin Numbers & Functions

68 Pins — CQFP Package

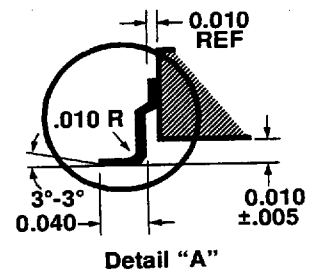
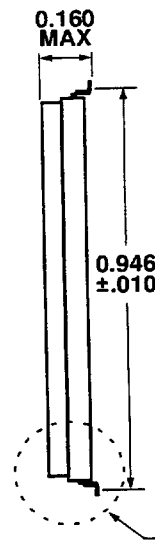
Pin#	Function	Pin#	Function	Pin#	Function	Pin#	Function
1	GND	18	GND	35	\overline{OE}	52	GND
2	\overline{CE}_3	19	I/O8	36	\overline{CE}_2	53	I/O23
3	A5	20	I/O9	37	A17	54	I/O22
4	A4	21	I/O10	38	\overline{WE}_2	55	I/O21
5	A3	22	I/O11	39	\overline{WE}_3	56	I/O20
6	A2	23	I/O12	40	\overline{WE}_4	57	I/O19
7	A1	24	I/O13	41	A18	58	I/O18
8	A0	25	I/O14	42	NC	59	I/O17
9	NC	26	I/O15	43	NC	60	I/O16
10	I/O0	27	V _{CC}	44	I/O31	61	V _{CC}
11	I/O1	28	A11	45	I/O30	62	A10
12	I/O2	29	A12	46	I/O29	63	A9
13	I/O3	30	A13	47	I/O28	64	A8
14	I/O4	31	A14	48	I/O27	65	A7
15	I/O5	32	A15	49	I/O26	66	A6
16	I/O6	33	A16	50	I/O25	67	\overline{WE}_1
17	I/O7	34	\overline{CE}_1	51	I/O24	68	\overline{CE}_4

"F5" — Single-Cavity CQFP

Top View



Side View



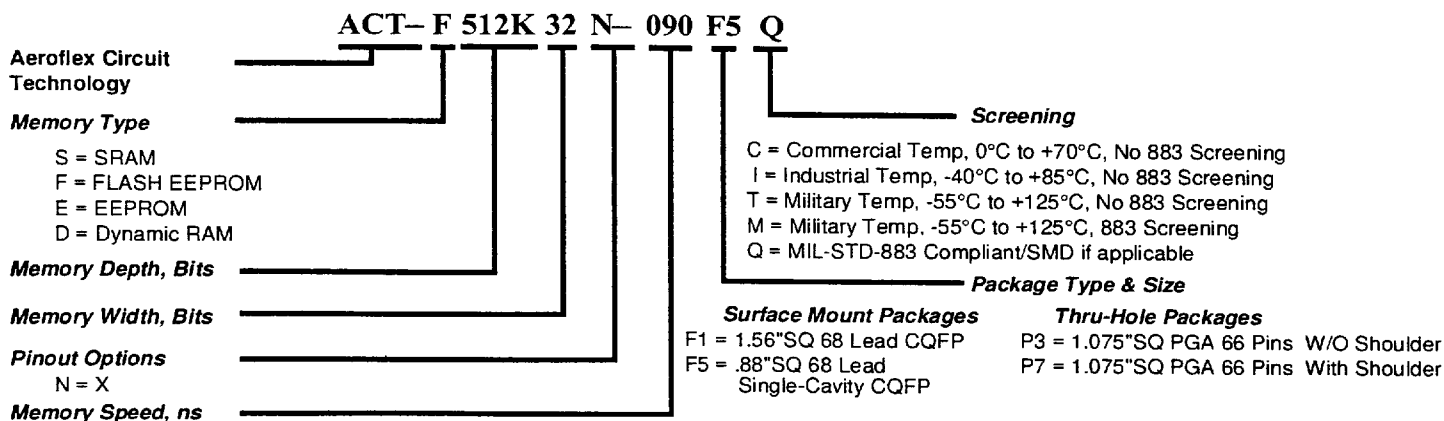
All dimensions in inches



Ordering Information

Model Number	DESC Drawing Number	Speed	Package
ACT-F512K32N-070P3Q	5962-9461204HXX	70 nS	PGA
ACT-F512K32N-090P3Q	5962-9461203HXX	90 nS	PGA
ACT-F512K32N-120P3Q	5962-9461202HXX	120 nS	PGA
ACT-F512K32N-150P3Q	5962-9461201HXX	150 nS	PGA
ACT-F512K32N-070P7Q	5962-9461204HUX	70 nS	PGA
ACT-F512K32N-090P7Q	5962-9461203HUX	90 nS	PGA
ACT-F512K32N-120P7Q	5962-9461202HUX	120 nS	PGA
ACT-F512K32N-150P7Q	5962-9461201HUX	150 nS	PGA
ACT-F512K32N-070F1Q	5962-9461204HTX (Pending)	70 nS	CQFP
ACT-F512K32N-090F1Q	5962-9461203HTX (Pending)	90 nS	CQFP
ACT-F512K32N-120F1Q	5962-9461202HTX (Pending)	120 nS	CQFP
ACT-F512K32N-150F1Q	5962-9461201HTX (Pending)	150 nS	CQFP
ACT-F512K32N-070F5Q	5962-9461204HMX	70 nS	CQFP
ACT-F512K32N-090F5Q	5962-9461203HMX	90 nS	CQFP
ACT-F512K32N-120F5Q	5962-9461202HMX	120 nS	CQFP
ACT-F512K32N-150F5Q	5962-9461201HMX	150 nS	CQFP

Part Number Breakdown



Specification subject to change without notice

Aeroflex Circuit Technology
35 South Service Road
Plainview New York 11830

Telephone: (516) 694-6700
FAX: (516) 694-6715
Toll Free Inquiries: 1-(800) 843-1553